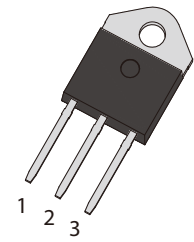


FEATURES

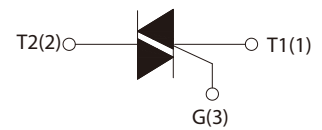
- | High current 40 A RMS current Triac
- | Low thermal resistance
- | High commutation or very high commutation capability
- | RoHS (2002/95/EC) compliant packages
- | UL-94, V0 flammability package resin compliance



TO-3P

APPLICATIONS

- | General purpose motor control circuits
- | Phase control operations in light dimmers and motor speed controllers
- | Home appliances



Schematic Symbol

APPROVALS

RoHS	Compliance with 2011/65/EU
HF	Compliance with IEC61249-2-21:2003

THE MAIN PARAMETERS

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current	40	A
V_{DRM}	Off-state repetitive peak voltage	1200	V
V_{TM}	On-state voltage	1.5	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1200	V
RMS on-state current ($T_c=90^\circ\text{C}$)	$I_{\text{T(RMS)}}$	40	A
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)	I_{TSM}	400	
I^2t value for fusing ($t_p=10\text{ms}$)	I^2t	880	A^2S
Critical rate of rise of on-state current ($I_G=2 \cdot I_{\text{GT}}$)	d/d_t	50	$\text{A}/\mu\text{s}$
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{\text{G(AV)}}$	1	W
Storage junction temperature range	T_{STG}	-40~+150	$^\circ\text{C}$
Operating junction temperature range	T_j	-40~+125	

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
			B	C	
I_{GT}	$V_D=12\text{V}, R_L=33\Omega$	I - II - III	≤ 50	≤ 25	mA
		IV	≤ 70	≤ 50	
V_{GT}		ALL	≤ 1.3		V
V_{GD}	$V_D=V_{\text{DRM}}, R_L=3.3\text{K}\Omega, T_j=125^\circ\text{C}$	ALL	≥ 0.2		V
I_{H}	$I_T=100\text{mA}$		≤ 80	≤ 30	mA
I_{L}	$I_G=1.2I_{\text{GT}}$	I - III - IV	≤ 90	≤ 60	
		II	≤ 100	≤ 80	
dV_D/dt	$V_D=67\%V_{\text{DRM}}, T_j=125^\circ\text{C}$		≥ 1000	≥ 500	$\text{V}/\mu\text{s}$
V_{TM}	$I_{\text{TM}}=60\text{A}, t_p=380\mu\text{s}$		≤ 1.5		V
I_{DRM}	$V_D=V_{\text{DRM}}, V_R=V_{\text{RRM}}$	$T_j=25^\circ\text{C}$	≤ 10		μA
I_{RRM}		$T_j=125^\circ\text{C}$	≤ 5		mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case(AC)	1.1	$^{\circ}\text{C}/\text{W}$

PARAMETER CHARACTERISTIC CURVE

FIG.1 Maximum power dissipation versus RMS on-state current

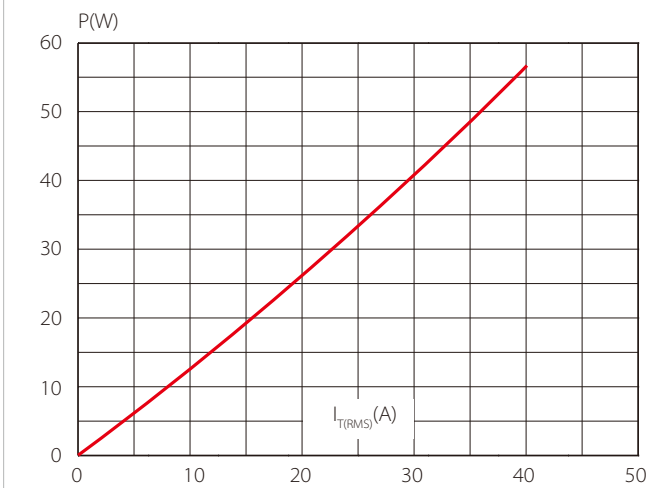


FIG.2: RMS on-state current versus case temperature

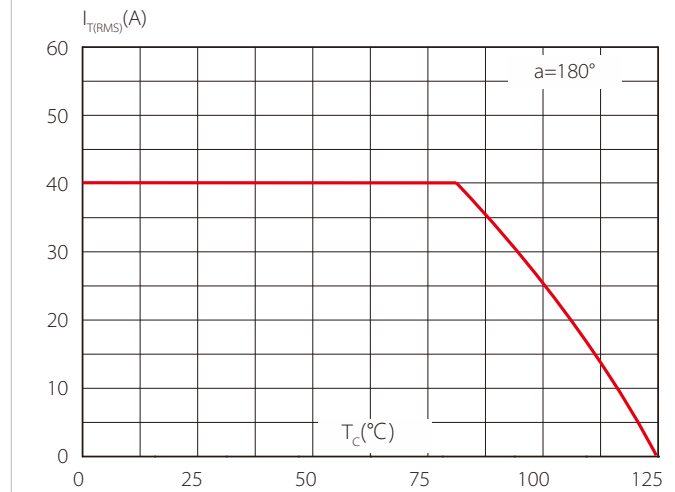


FIG.3: Surge peak on-state current versus number of cycles

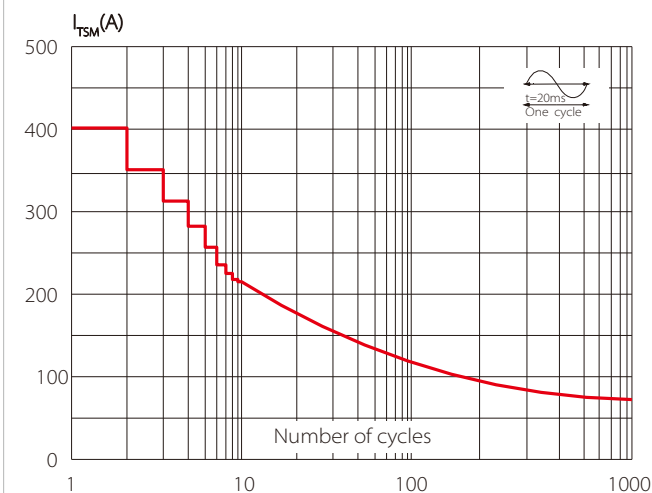


FIG.4 On-state characteristics (maximum values)

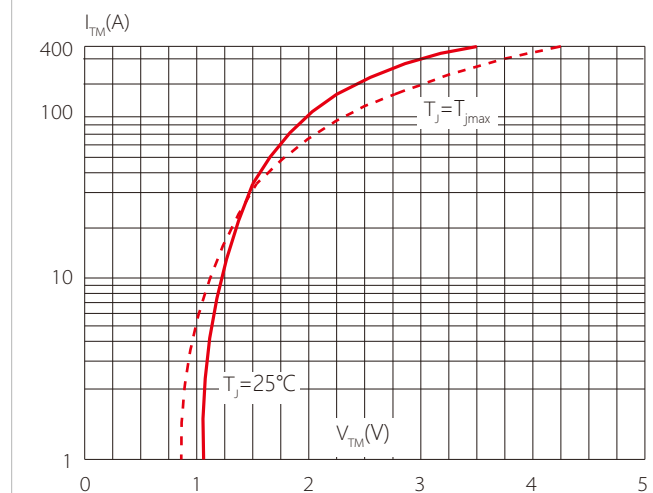


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

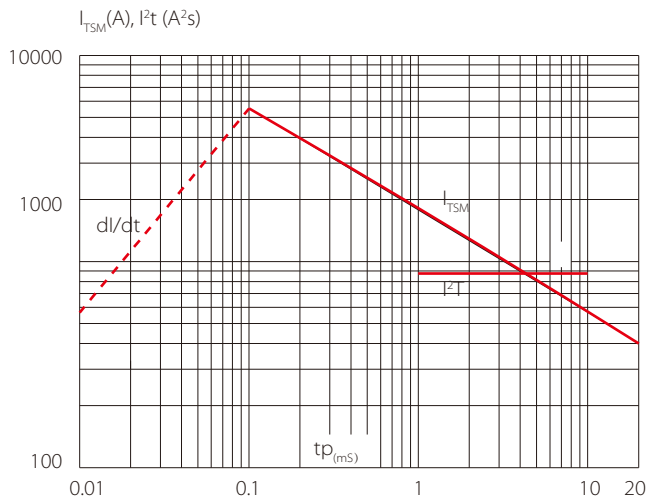


FIG.6 Relative variations of gate trigger current versus junction temperature

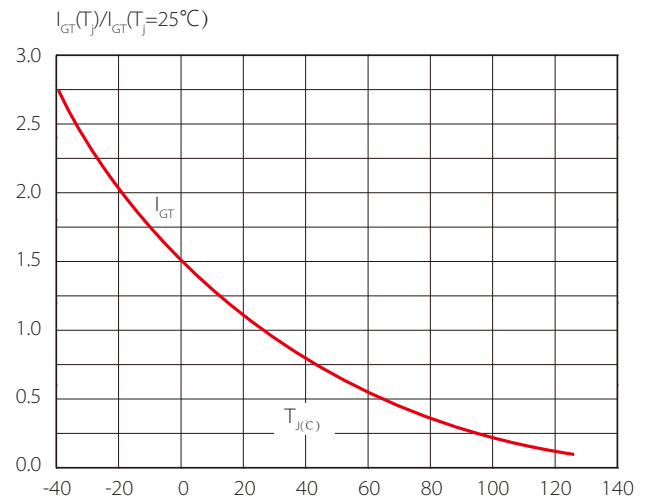


FIG.7 Relative variations of holding current versus junction temperature

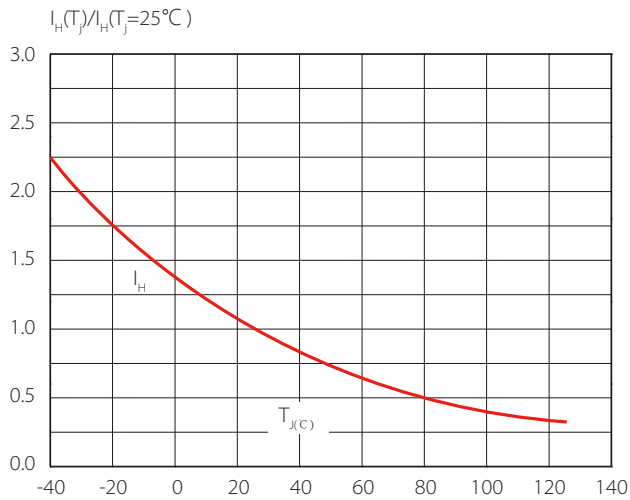
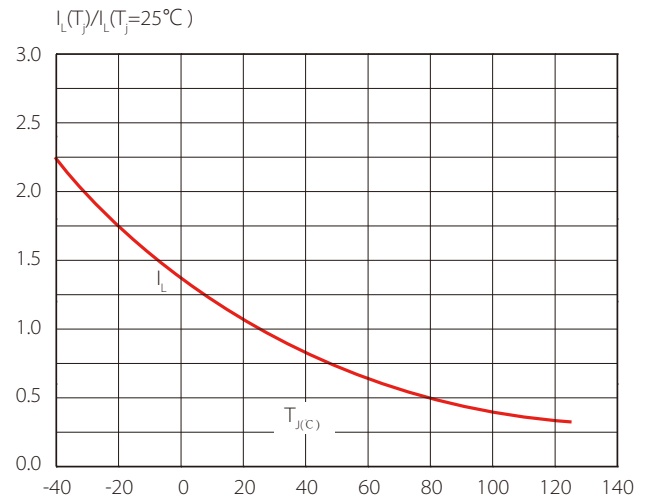
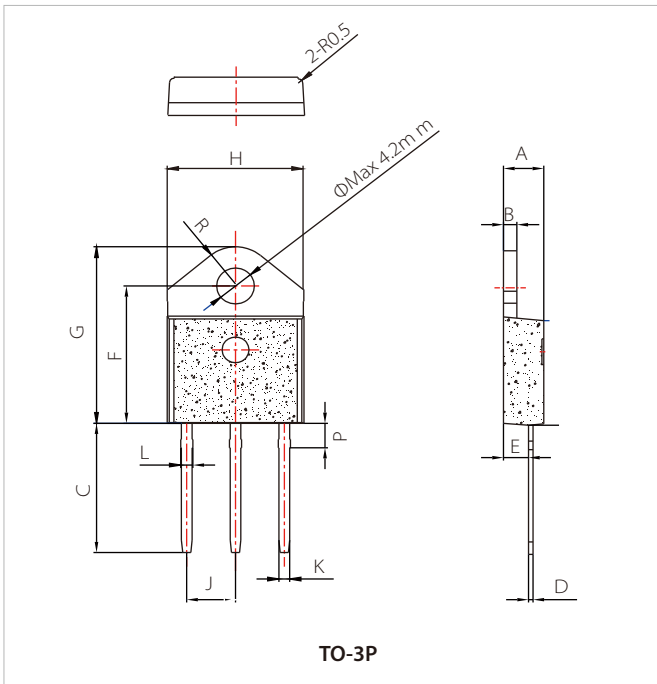


FIG.8 Relative variations of latching current versus junction temperature



PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.35		1.50	0.053		0.059
P	2.80		3.00	0.110		0.118
R		4.35			0.171	

ORDERING INFORMATION

Part Number	Package	Qty/pcs		
		Tube	Inner Box	Carton
STZ40Q120B(C)	TO-3P	30	450	3600

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